

FEATURES

- | Glass-passivated mesa chip for reliability and uniform
- | High current output up to 4.0 A
- | RoHS (2002/95/EC) compliant packages

APPLICATIONS

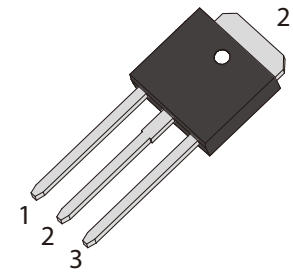
- | Flash lamp
- | Electronic ballast
- | Igniter

APPROVALS

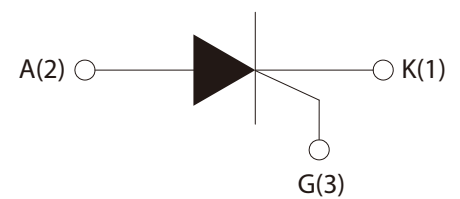
| | |
|-------------|------------------------------------|
| RoHS | Compliance with 2011/65/EU |
| HF | Compliance with IEC61249-2-21:2003 |

ABSOLUTE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|--|---------------------|----------|------------------------|
| Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$) | V_{DRM} | 800 | V |
| Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$) | V_{RRM} | 800 | |
| RMS on-state current ($T_c=90^\circ\text{C}$) | $I_{\text{T(RMS)}}$ | 4 | A |
| Non repetitive surge peak on-state current ($t_p=10\text{ms}$) | I_{TSM} | 30 | |
| I^2t value for fusing ($t_p=10\text{ms}$) | I^2t | 4.5 | A^2S |
| Critical rate of rise of on-state current ($I_G=2*I_{GT}$) | d/d_t | 50 | $\text{A}/\mu\text{s}$ |
| Peak gate current | I_{GM} | 1.2 | A |
| Average gate power dissipation | $P_{\text{G(AV)}}$ | 0.2 | W |
| Storage junction temperature range | T_{STG} | -40~+150 | °C |
| Operating junction temperature range | T_j | -40~+125 | |



TO-251



Schematic Symbol

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

| Symbol | Test Condition | Value | | | Unit |
|-----------|---|-------|------|------|------------------------|
| | | Min. | Typ. | Max. | |
| I_{GT} | $V_D=12\text{V}, R_L=33\Omega$ | - | 50 | 200 | μA |
| V_{GT} | | - | 0.6 | 0.8 | V |
| V_{GD} | $V_D=V_{DRM}, R_L=3.3\text{K}\Omega, T_j=150^{\circ}\text{C}$ | 0.2 | - | - | |
| I_H | $I_T=500\text{mA}$ | - | - | 5 | mA |
| I_L | $I_G=1.2I_{GT}$ | - | - | 6 | |
| dV_D/dt | $V_D=2/3V_{DRM}, R_{GK}=1\text{K}\Omega, T_j=125^{\circ}\text{C}$ | 10 | - | - | $\text{V}/\mu\text{s}$ |

STATIC CHARACTERISTICS

| Symbol | Parameter | Value | Unit | |
|-----------|--|---------------------------|------------|---------------|
| V_{TM} | $I_{TM}=8\text{A}, t_p=380\mu\text{s}$ | $T_j=25^{\circ}\text{C}$ | ≤ 1.5 | V |
| I_{DRM} | $V_D=V_{DRM}, V_R=V_{RRM}$ | | ≤ 5 | μA |
| I_{RRM} | | $T_j=125^{\circ}\text{C}$ | ≤ 100 | μA |

THERMAL RESISTANCES

| Symbol | Parameter | Value | Unit |
|---------------|----------------------|-------|-----------------------------|
| $R_{th(j-c)}$ | Junction to case(AC) | 6.5 | $^{\circ}\text{C}/\text{W}$ |

PARAMETER CHARACTERISTIC CURVE

FIG.1 Maximum power dissipation versus RMS on-state current

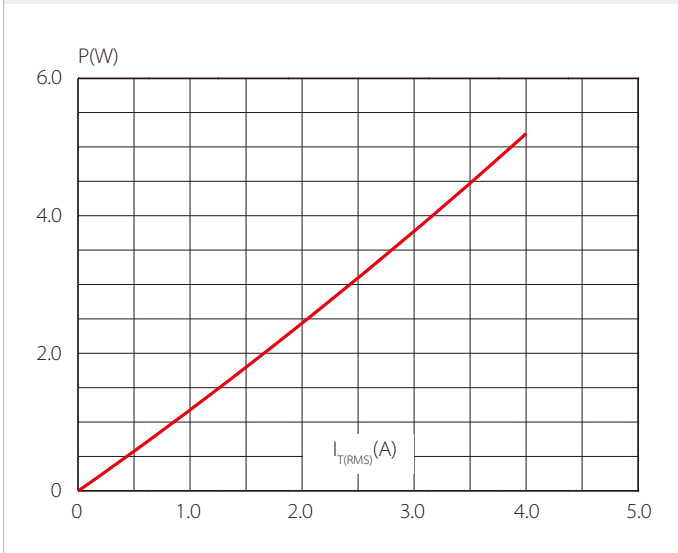


FIG.2: RMS on-state current versus case temperature

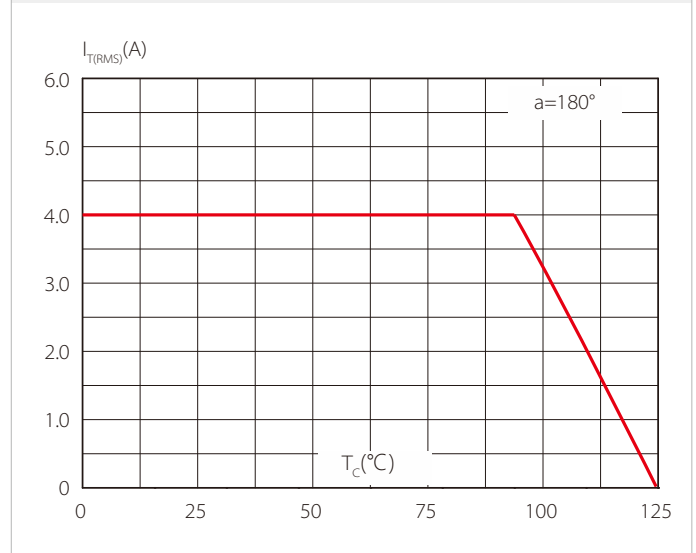


FIG.3: Surge peak on-state current versus number of cycles

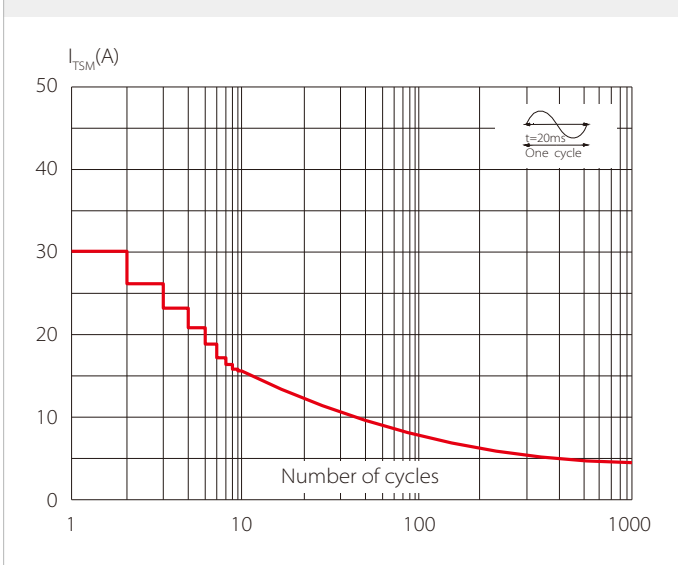


FIG.4 On-state characteristics (maximum values)

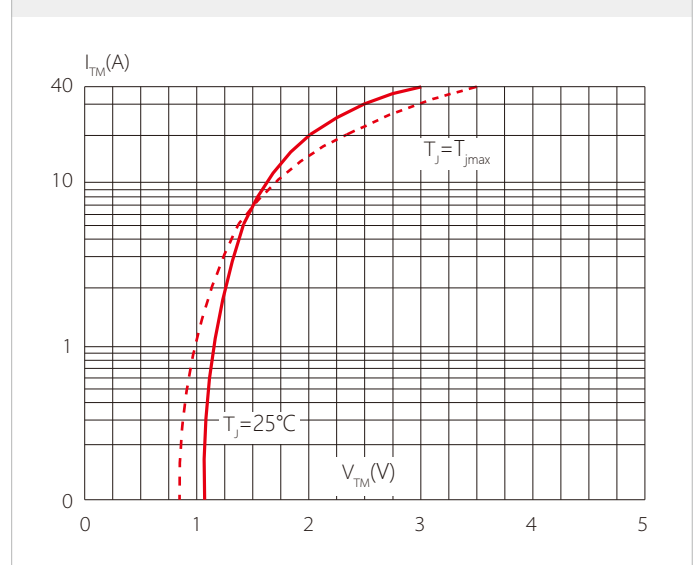


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$ and corresponding value of I^2t ($dI/dt < 50\text{A}/\mu\text{s}$)

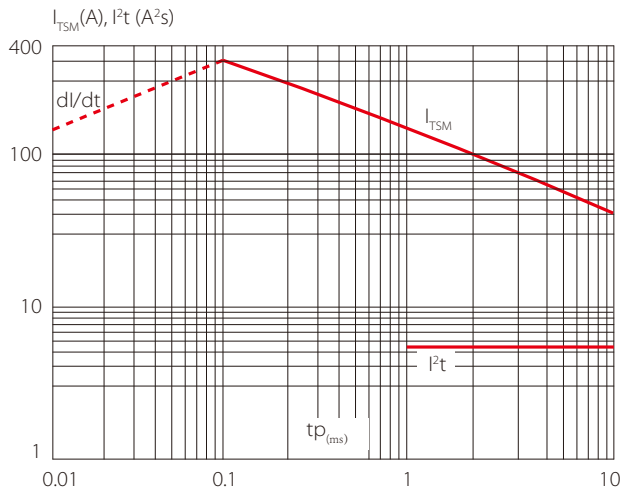


FIG.6 Relative variations of gate trigger current versus junction temperature

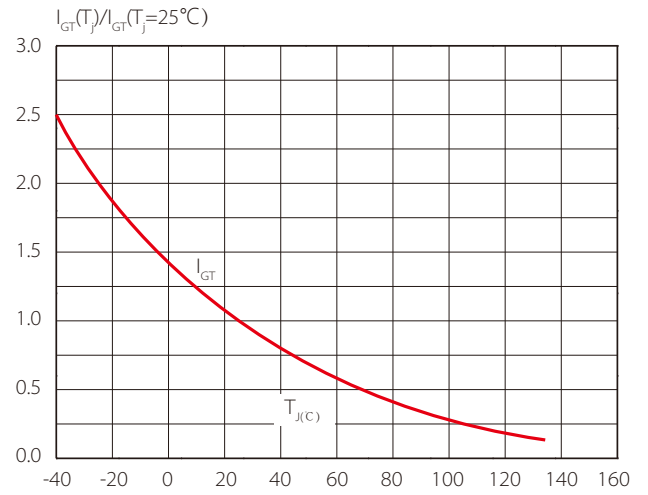


FIG.7 Relative variations of holding current versus junction temperature

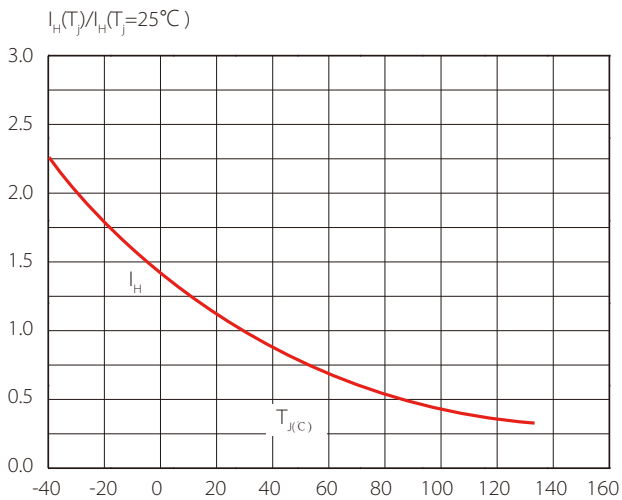
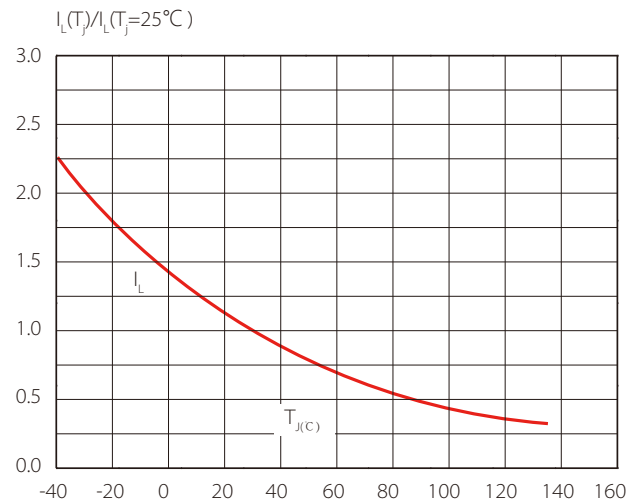
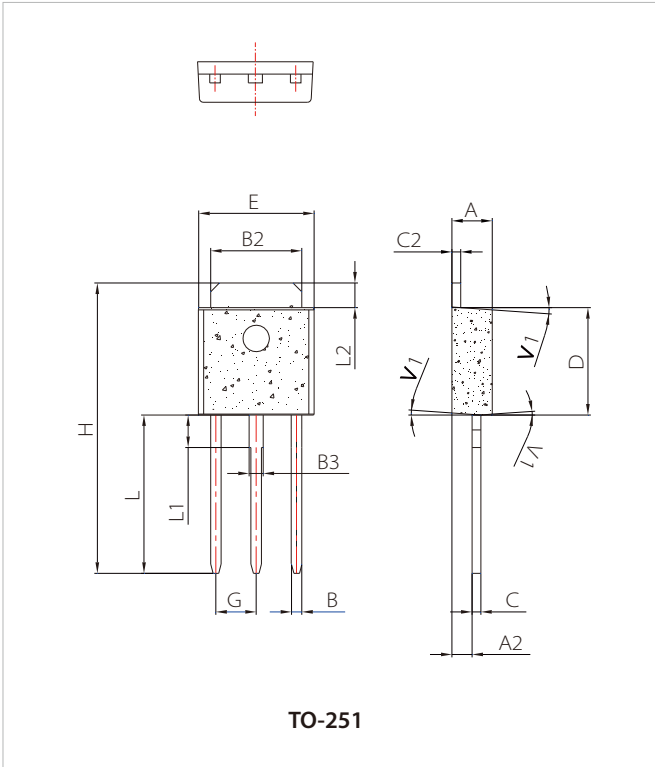


FIG.8 Relative variations of latching current versus junction temperature



PACKAGE MECHANICAL DATA



| Ref. | Dimensions | | | | | |
|------|-------------|------|------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 2.20 | | 2.40 | 0.086 | | 0.095 |
| A2 | 0.90 | | 1.20 | 0.035 | | 0.047 |
| B | 0.55 | | 0.65 | 0.022 | | 0.026 |
| B2 | 5.10 | | 5.40 | 0.200 | | 0.213 |
| B3 | 0.76 | | 0.85 | 0.030 | | 0.033 |
| C | 0.45 | | 0.62 | 0.018 | | 0.024 |
| C2 | 0.48 | | 0.62 | 0.019 | | 0.024 |
| D | 6.00 | | 6.20 | 0.236 | | 0.244 |
| E | 6.40 | | 6.70 | 0.252 | | 0.264 |
| G | | 2.30 | | | 0.091 | |
| H | 16.0 | | 17.0 | 0.630 | | 0.669 |
| L | 8.90 | | 9.40 | 0.350 | | 0.370 |
| L1 | 1.80 | | 1.90 | 0.071 | | 0.075 |
| L2 | 1.37 | | 1.50 | 0.054 | | 0.059 |
| V1 | | 4° | | | 4° | |

ORDERING INFORMATION

| Part Number | Package | Qty/pcs | | |
|-------------|---------|---------|-----------|--------|
| | | Tube | Inner Box | Carton |
| SCH4M80 | TO-251 | 80 | 4000 | 32000 |

Headquarters

No.3387 Shendu Road Pujiang
I&E Park
Minhang Shanghai China
201000

Hotline

400-021-5756

Web

<https://www.semiware.com>

Sales center

Tel: 86-21-3463-7458
Email: sales18@semiware.com

Customer Service

Tel: 86-21-5484-1001
Email: sales17@semiware.com

Technical Support

Tel: 86-21-3463-7654
Email: fae01@semiware.com

Complaint & Suggestions

Tel: 86-21-3463-7172
Ext: 8868
Email: cs03@semiware.com

By QR Code

Website



Wechat

To find your local partner within Semiware's global network: www.semiware.com

© 2022 Semiware Semiconductor Inc.

The content of this document has been carefully checked and understood. However, neither Semiware nor its subsidiaries assume any liability whatsoever for any errors or inaccuracies of this document and the consequences thereof. Published specifications are subject to change without notice. Product suitability for any area of application must ultimately be determined by the customer. In all cases, products must never be operated outside their published specifications. Semiware does not guarantee the availability of all published products. This disclaimer shall be governed by substantive Swiss law and resulting disputes shall be settled by the courts at the place of business of Semiware. Latest publications and a complete disclaimer can be downloaded from the Semiware website. All trademarks recognized.